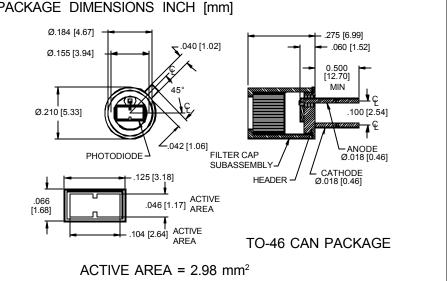
PHOTONIC
Silicon Photodiode, Filter Combination Photoconductive
DETECTORS INC.600 nm (red color) Type PDV-C403-46



PACKAGE DIMENSIONS INCH [mm]



RESPONSIVITY (A/W)

FEATURES

- 600 nm CWL
- 65 nm FWHM
- Low noise
- The **PDV-C403-46** is a silicon, PIN planar diffused, photodiode with a red color 600 nm +/- 2 nm CWL wide band interference filter and a wide 65 nm half bandwidth. Ideal for photometry and radiometry measurment applications.

APPLICATIONS

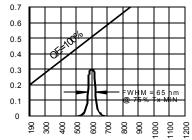
- Red color matching
- Color meters
- Film processing

ABSOLUTE MAXIMUM RATING (TA=25°C unless otherwise noted)

DESCRIPTION

SYMBOL	PARAMETER	MIN	MAX	UNITS
Vbr	Reverse Voltage		100	V
T _{STG}	Storage Temperature	-20	+85	$^{\circ}$ C
To	Operating Temperature Range	-15	+70	°C
Ts	Soldering Temperature*		+240	°C
Ι	Light Current		500	mA

SPECTRALRESPONSE



WAVELENGTH(nm)

*1/16 inch from case for 3 secs max

ELECTRO-OPTICAL CHARACTERISTICS (TA=25°C unless otherwise noted)

SYMBOL	CHARACTERISTIC	TESTCONDITIONS	MIN	TYP	MAX	UNITS				
lsc	Short Circuit Current***	H = 100 fc, 2850 K	40	45		μ A				
l d	Dark Current	H = 0, V _R = 10 V		.15	1.0	nA				
Rsh	Shunt Resistance	H = 0, V _R = 10 mV	.5	1.0		GΩ				
TC Rsh	RsH Temp. Coefficient	H = 0, V _R = 10 mV		-8		% / °C				
CJ	Junction Capacitance	H = 0, V _R = 10 V**		10		pF				
CWL	Center Wavelength	(CWL, λ o) +/- 2 nm		600		nm				
HBW	Half Bandwidth	(FWHM)		65		nm				
Vbr	Breakdown Voltage	I = 10 μA	70	100		V				
NEP	Noise Equivalent Power	V _R = 10 V @ Peak		1.5x10 ⁻¹⁴		W/√ ^{Hz}				
tr	Response Time	RL = 1 KΩ V _R = 50 V		10		nS				

Information in this technical data sheet is believed to be correct and reliable. However, no responsibility is assumed for possible inaccuracies or omission. Specifications are subject to change without notice.**f=1 MHz, *** without filter [FORM NO. 100-PDV-C403-46 REV N/C]